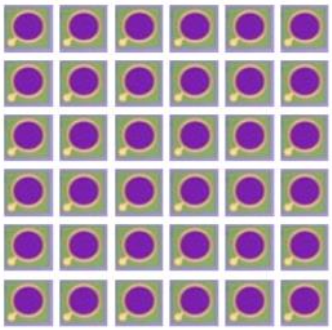
1260-1620nm InGaAs PIN Photodiode Chip, Dia. 300um Active Area

Part No. PDC-13A300



Features

- 1260nm~1620nm InGaAs PIN photodiode chip
- Dia. 300μm Active area
- Optimized for monitor application
- Low dark current and low capacitance

Specifications

Absolute Maximum Ratings				
Parameters	Min.	Max.	Unit	Conditions
Storage temperature	-40	100	ºC	
Operating temperature	-40	85	ºC	
Forward current		10	mA	
Reverse current		2	mA	
Reverse voltage		20	V	
Optical power		2	mW	
ESD	500		V	

Electro-Optical Characteristics						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Responsivity	R	0.8	1.0		A/W	V_R=5V, λ=1300nm at 25ºC
		0.9	1.1			V_R=5V, λ=1550nm at 25ºC
Dark current	I_D		0.3	1	nA	V_R=5V at 25ºC
Breakdown voltage	V_{BD}	25	35		V	I_R=1μA
Capacitance	C		6	10	pF	V_R=5V, f=1MHz

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Typical Characteristics

Fig. 1 Typical Dark Current vs. Forward Current

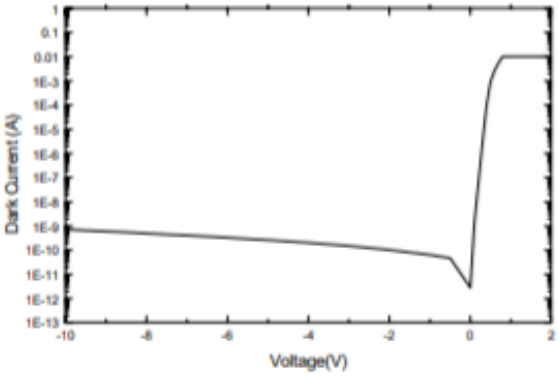


Fig. 2 Typical Photo-Current

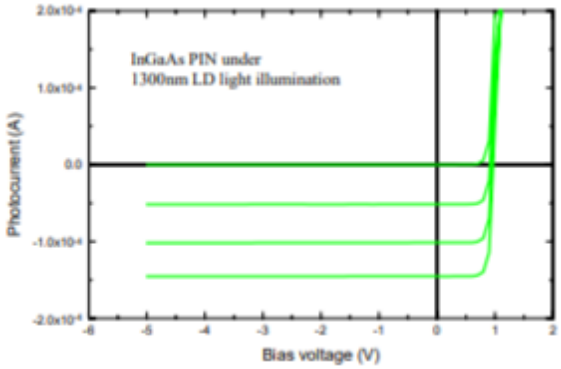


Fig. 3 Typical Breakdown Curve

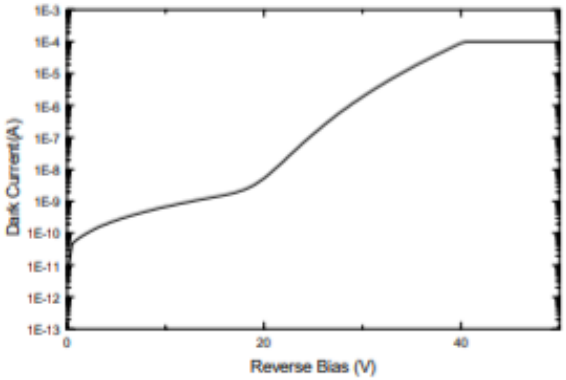
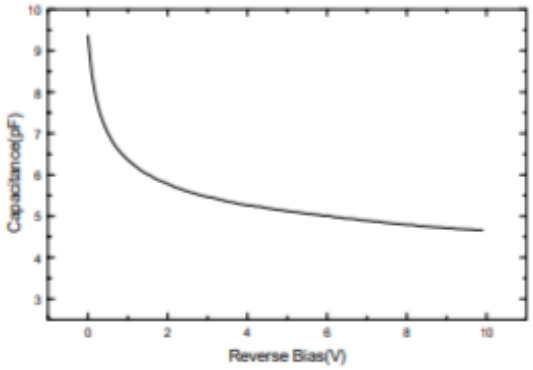
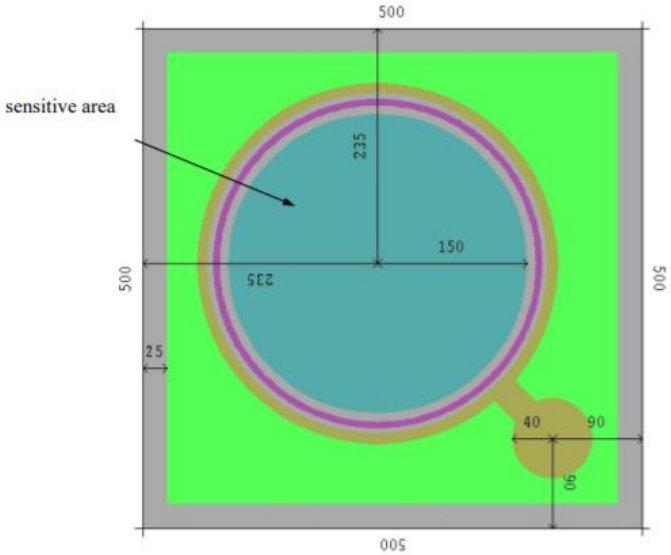


Fig. 4 Typical C-V Curve



Outline Diagram



- Chip size: 500μm x 500μm ±30μm typical
- Chip thickness: 200μm ±30μm
- Sensitive area: Typical 300μm ±5μm in diameter

Note: Specifications are subject to change without notice.

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